IXYS

Advance Technical Infomation

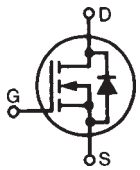
Trenchgate Power MOSFET

IXTQ82N28T

V_{DSS} = 280 V
I_{D25} = 82 A
$R_{DS(on)}$ = 44 mΩ

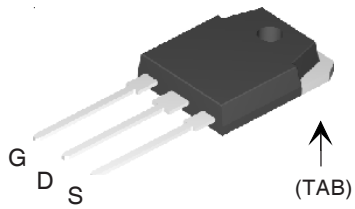
N-Channel Enhancement Mode

For Plasma Display Application



Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	T_J = 25°C to 150°C	280	V
V_{DGR}	T_J = 25°C to 150°C; R_{GS} = 1 MΩ	280	V
V_{GS}	Continuous	±20	V
V_{GSM}	Transient	±25	V
I_{D25}	T_C = 25°C	82	A
I_{D25}	External lead current limit	75	A
I_{DM}	T_C = 25°C, pulse width limited by T_{JM}	240	A
dv/dt	$I_S \le I_{DM}$, di/dt ≤ 100 A/μs, $V_{DD} \le V_{DSS}$ $T_J \le 150°C$, R_G = 4 Ω	5	V/ns
P_D	T_C = 25°C	540	W
T_J		-55 ... +150	°C
T_{JM}		150	°C
T_{stg}		-55 ... +150	°C
T_L	1.6 mm (0.062 in.) from case for 10 s	300	°C
M_d	Mounting torque (TO-3P)	1.13/10	Nm/lb.in.
Weight		5.5	g

TO-3P (IXTQ)



G = Gate D = Drain
S = Source TAB = Drain

Features

- Trench gate construction for low $R_{DS(on)}$
- International standard package
- Low package inductance
  - easy to drive and to protect

Advantages

- Easy to mount
- Space savings
- High power density

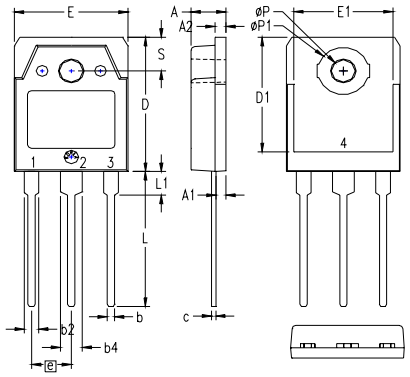
Symbol (T_J = 25°C, unless otherwise specified)	Test Conditions	Characteristic Values Min.	Typ.	Max.	
V_{DSS}	V_{GS} = 0 V, I_D = 250 μA	280			V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, I_D = 250μA	2.5		4.5	V
I_{GSS}	V_{GS} = ±20 V_{DC}, V_{DS} = 0			±100	nA
I_{DSS}	$V_{DS} = V_{DSS}$ V_{GS} = 0 V T_J = 125°C			1 200	μA μA
$R_{DS(on)}$	V_{GS} = 10 V, $I_D = 0.5\ I_{D25}$ Pulse test, t ≤ 300 μs, duty cycle d ≤ 2 %			49	mΩ

Symbol	Test Conditions (T_J = 25°C, unless otherwise specified)	Characteristic Values Min.	Typ.	Max.	
g_{fs}	V_{DS}= 10 V; I_D = 0.5 I_{D25}, pulse test	40	68		S
C_{iss}	V_{GS} = 0 V, V_{DS} = 25 V, f = 1 MHz		5326		pF
C_{oss}			609		pF
C_{rss}			38		pF
$t_{d(on)}$	V_{GS} = 10 V, V_{DS} = 0.5 V_{DSS}, I_D = I_{D25} R_G = 4 Ω (External)		33		ns
t_r			60		ns
$t_{d(off)}$			46		ns
t_f			46		ns
$Q_{g(on)}$	V_{GS}= 10 V, V_{DS} = 0.5 V_{DSS}, I_D = 0.5 I_{D25}		156	180	nC
Q_{gs}			46		nC
Q_{gd}			43		nC
R_{thJC}				0.23	K/W
R_{thCK}			0.21		K/W

Source-Drain Diode

Symbol	Test Conditions (T_J = 25°C, unless otherwise specified)	Characteristic Values Min.	typ.	Max.	
I_S	V_{GS} = 0 V			82	A
I_{SM}	Repetitive			240	A
V_{SD}	I_F = I_S, V_{GS} = 0 V, Pulse test, t ≤ 300 µs, duty cycle d ≤ 2 %			1.5	V
T_{JM}	I_F = 25 A -di/dt = 100 A/µs		250		ns
Q_{RM}	V_R = 100 V		3.0		µC

TO-3P (IXTQ) Outline



1 – GATE
2 – DRAIN (COLLECTOR)
3 – SOURCE (EMITTER)
4 – DRAIN (COLLECTOR)

SYM	INCHES MIN	INCHES MAX	MILLIMETERS MIN	MILLIMETERS MAX
A	.185	.193	4.70	4.90
A1	.051	.059	1.30	1.50
A2	.057	.065	1.45	1.65
b	.035	.045	0.90	1.15
b2	.075	.087	1.90	2.20
b4	.114	.126	2.90	3.20
c	.022	.031	0.55	0.80
D	.780	.791	19.80	20.10
D1	.665	.677	16.90	17.20
E	.610	.622	15.50	15.80
E1	.531	.539	13.50	13.70
e	.215 BSC		5.45 BSC	
L	.779	.795	19.80	20.20
L1	.134	.142	3.40	3.60
øP	.126	.134	3.20	3.40
øP1	.272	.280	6.90	7.10
S	.193	.201	4.90	5.10

All metal area are tin plated.

Fig. 1. Output Characteristics @ 25ºC

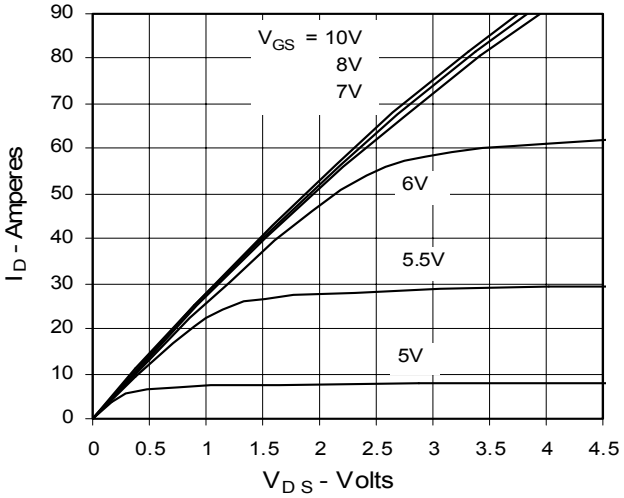


Fig. 2. Extended Output Characteristics @ 25ºC

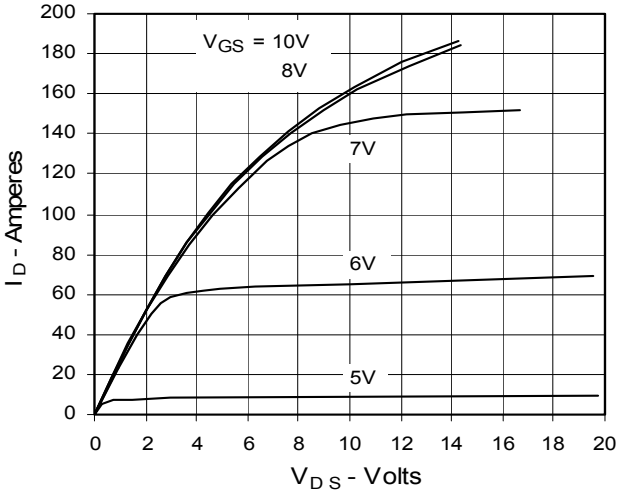


Fig. 3. Output Characteristics @ 125ºC

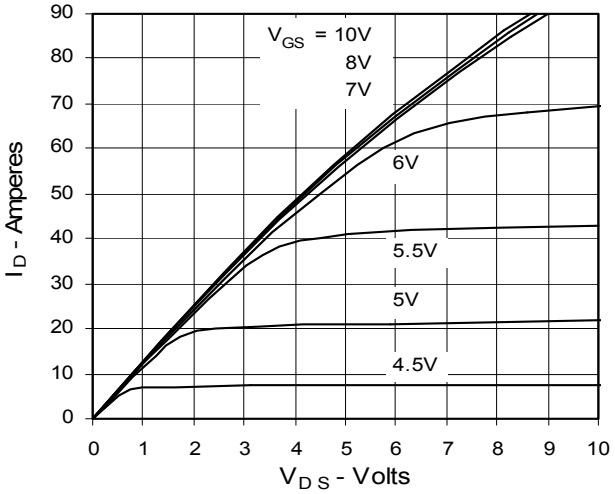


Fig. 4. $R_{DS(on)}$ Normalized to 0.5 I_{D25} Value vs. Junction Temperature

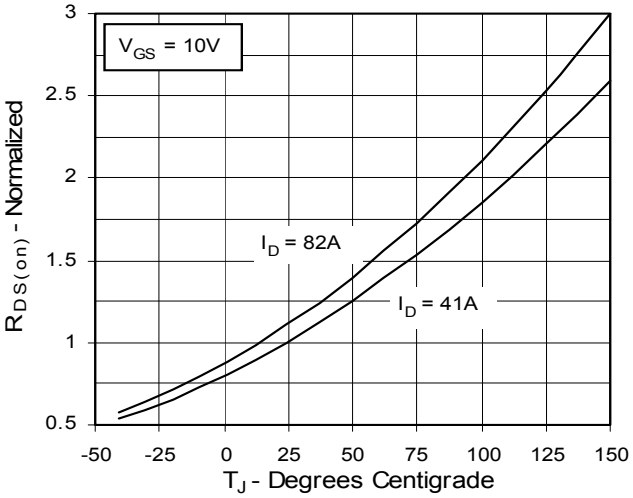


Fig. 5. $R_{DS(on)}$ Normalized to 0.5 I_{D25} Value vs. Drain Current

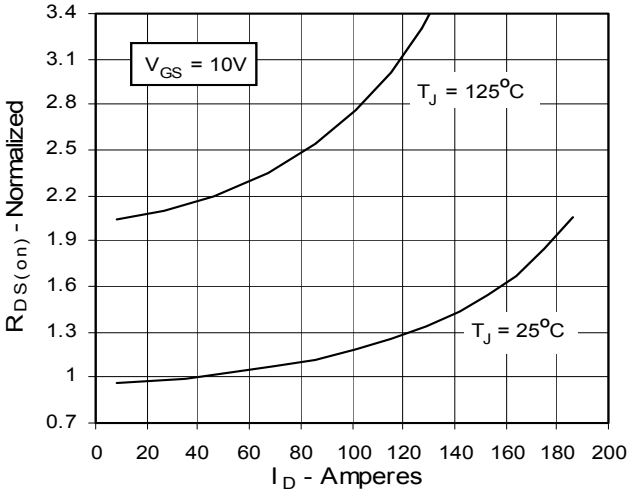


Fig. 6. Drain Current vs. Case Temperature

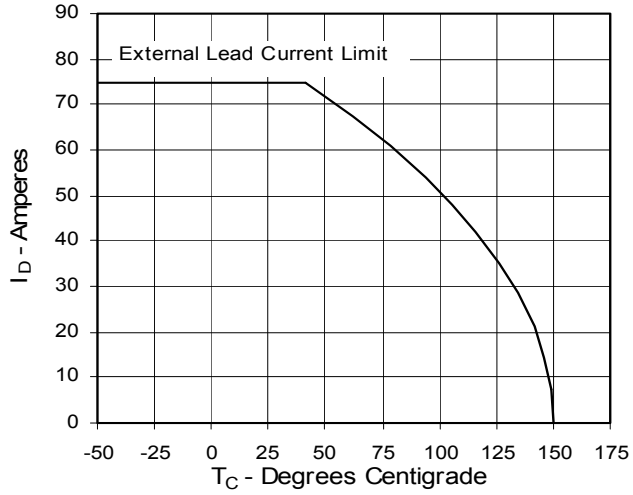


Fig. 7. Input Admittance

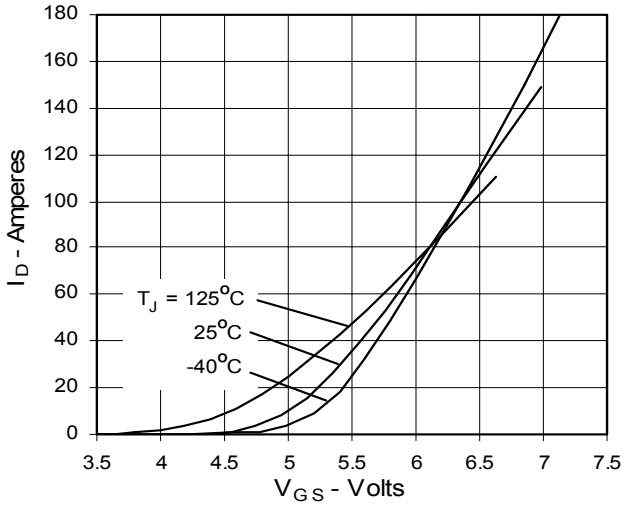


Fig. 8. Transconductance

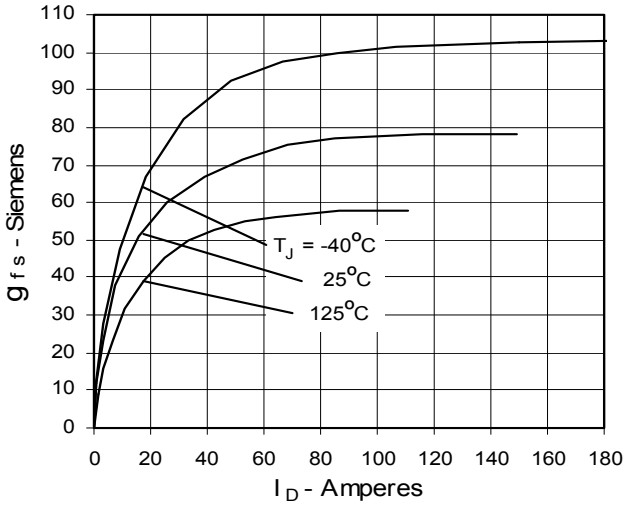


Fig. 9. Source Current vs. Source-To-Drain Voltage

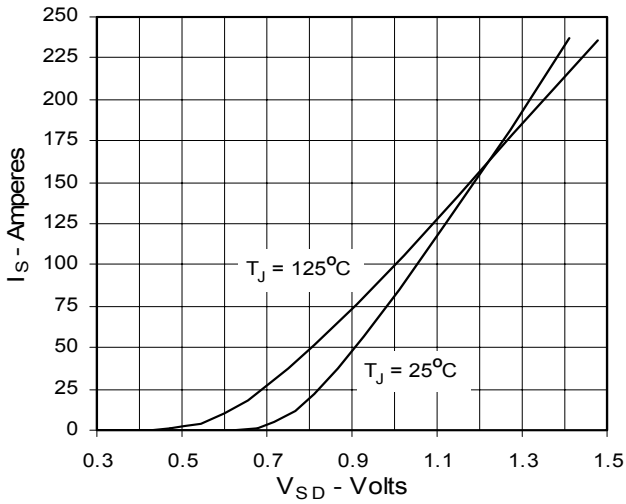


Fig. 10. Gate Charge

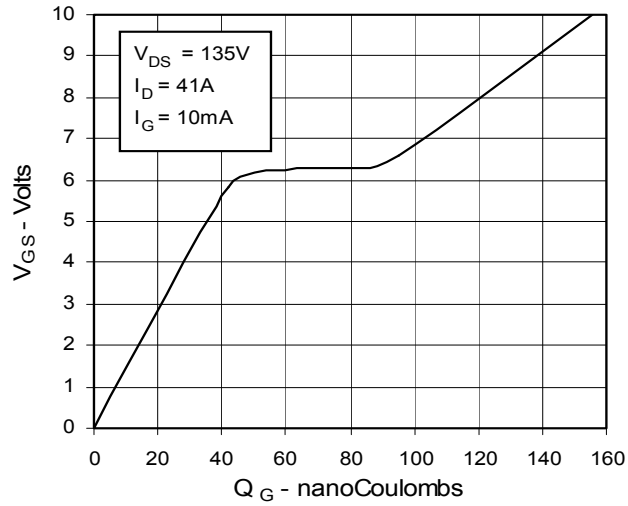


Fig. 11. Capacitance

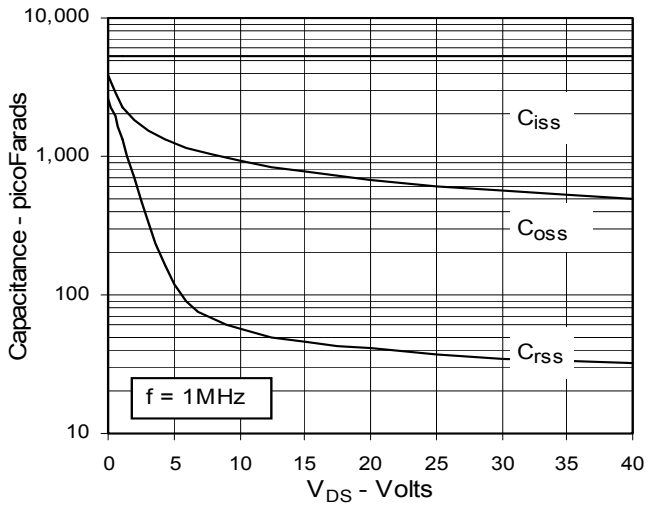


Fig. 12. Forward-Bias Safe Operating Area

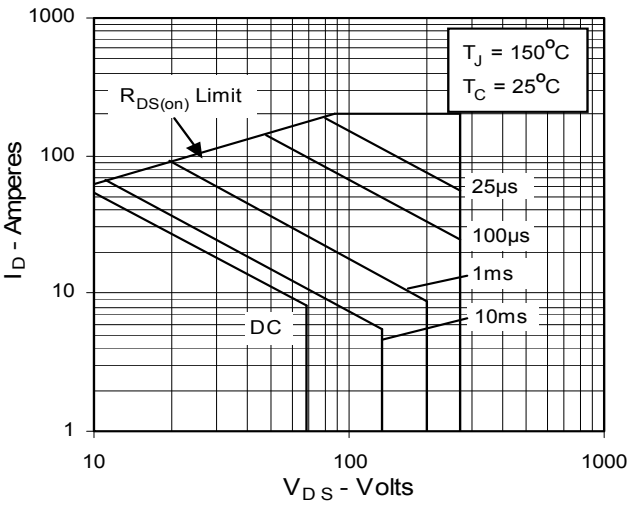


Fig. 13. Maximum Transient Thermal Resistance